Integrated Device Technology, Inc.

3.3V 64-BIT FLOW-THRU ERROR DETECTION AND CORRECTION UNIT

IDT49C3466

FEATURES:

- 64-bit wide Flow-thruEDC™
- Separate System and Memory Data Input/Output Buses
- — Error Detect Time: 20ns
  — Error Correct Time: 22ns
- Corrects all single bit errors; Detects all double bit errors and some multiple bit errors
- Configurable 16-deep bus read/write FIFOs with flags
- Simultaneous check bit generation and correction of memory data
- Supports partial word writes on byte boundaries
- Low noise output
- Sophisticated error diagnostics and error logging
- Parity generation on system data bus
- VCC = 3.3V ±0.3V
- 208-pin Plastic Quad Flatpack

DESCRIPTION:

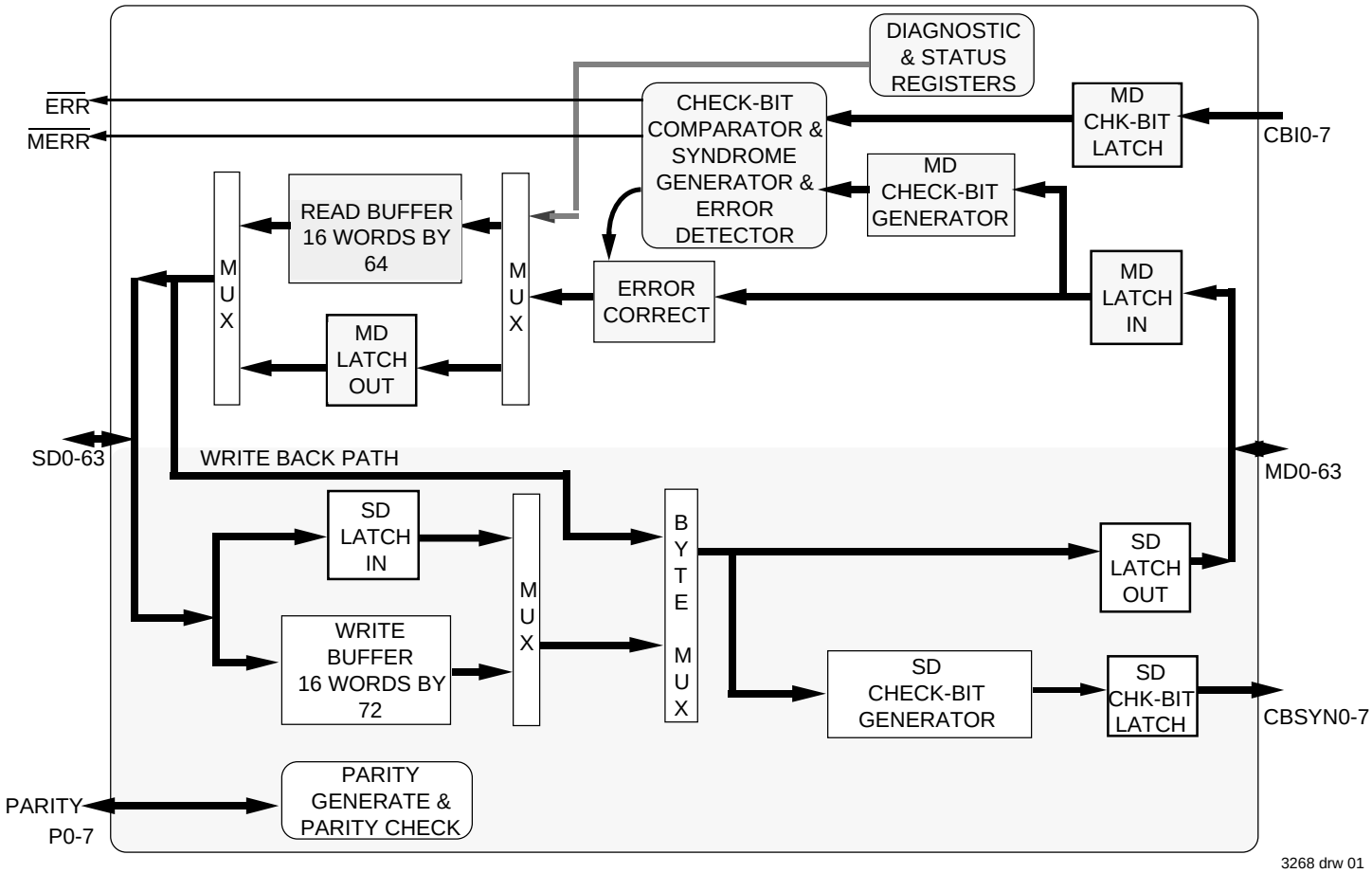
The IDT49C3466 64-bit Flow-thruEDC is a high-speed error detection and correction unit that ensures data integrity in memory systems. The flow-thru architecture, with separate system and memory data buses, is ideally suited for pipelined memory systems.

Implementing a modified Hamming code, the IDT49C3466 corrects all single bit hard and soft errors, and detects all double bit errors. The read/write FIFOs can store up to sixteen words. FIFO full and empty flags indicate whether additional data can be written to or read from the EDC.

Check bit generation for partial word writes on byte boundaries is supported on the IDT49C3466.

Diagnostic features include a check bit register, syndrome registers, a four bit error counter which logs up to 15 errors, and an error data register which stores the complete error data word. Parity can be generated and checked on the system bus by the IDT49C3466.

SIMPLIFIED FUNCTIONAL BLOCK DIAGRAM



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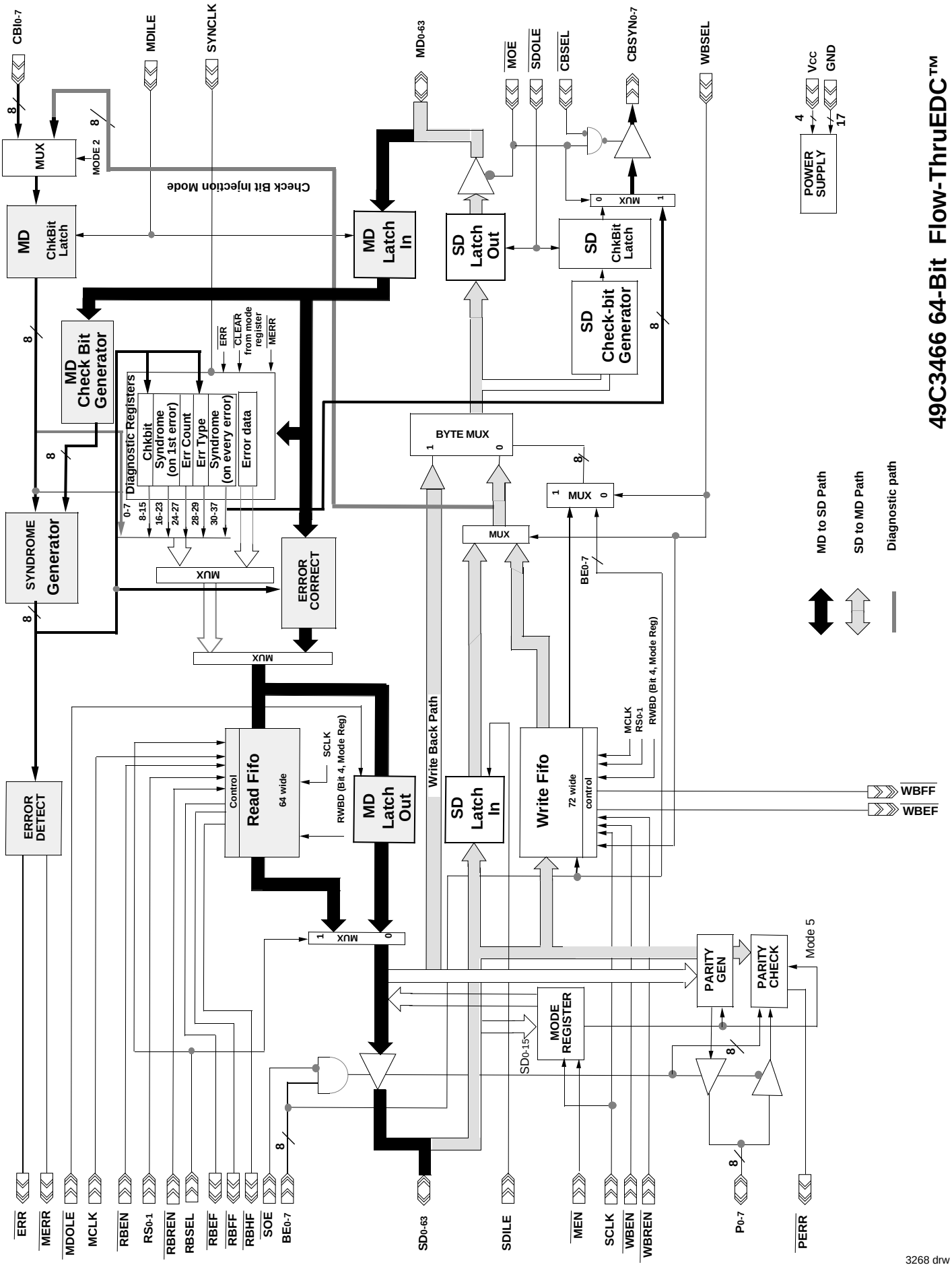
49C3466 64-Bit Flow-ThruEDC™
CBI0-7
MDILE
SYNCLK
MD0-63
MOE
SDOLE
CBSEL
CBSYN0-7
WBSEL
Vcc
GND
POWER SUPPLY
MUX
MODE 2
Check Bit Injection Mode
MD ChkBit Latch
MD Latch In
SD Latch Out
SD ChkBit Latch
SD Check-bit Generator
MD Check Bit Generator
ERR
CLEAR from mode register
MERR
Diagnostic Registers
Chkbit
Syndrome (on 1st error)
Err Count
Err Type
Syndrome (on every error)
Error data
0-7
8-15
16-23
24-27
28-29
30-37
BYTE MUX
SYNDROME Generator
ERROR CORRECT
BE0-7
Write Back Path
MCLK
RS0-1
RWBD (Bit 4, Mode Reg)
SCLK
Control
Read Fifo
64 wide
Write Fifo
72 wide
control
WBFF
WBEF
ERROR DETECT
MD Latch Out
SD Latch In
PARITY GEN
PARITY CHECK
Mode 5
MODE REGISTER
SD0-15
MD to SD Path
SD to MD Path
Diagnostic path
ERR
MERR
MDOLE
MCLK
RBEN
RS0-1
RBREN
RBSEL
RBEF
RBFF
RBHF
SOE
BE0-7
SD0-63
SDILE
MEN
SCLK
WBEN
WBREN
P0-7
PERR

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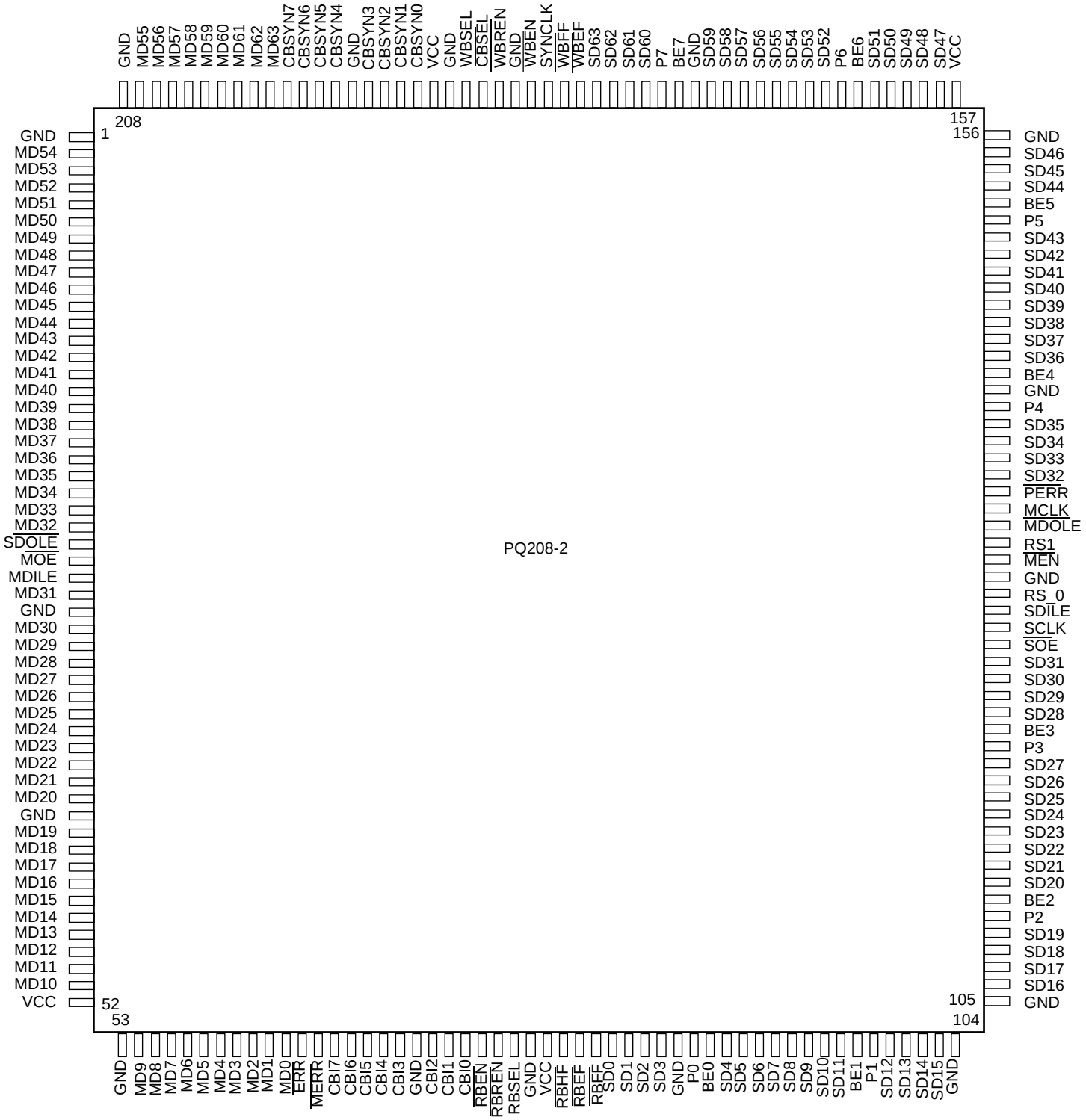
PIN CONFIGURATION



PQFP

Top View

3268 drw 03

PIN DESCRIPTION

Pin Name	I/O	Description
SD_{0-63}	I/O	**System Data Bus:** is a bidirectional 64-bit bus interfacing to the system or CPU. When System Output Enable, $\overline{SOE}$, is HIGH or Byte Enable, BE_{0-7}, is LOW, data can be input. When System Output Enable, $\overline{SOE}$, is LOW and Byte Enable, BE_{0-7}, is HIGH, the SD bus output drivers are enabled.
MD_{0-63}	I/O	**Memory Data Bus:** is a bidirectional 64-bit bus interfacing to the memory. During a read cycle, ($\overline{MOE}$ HIGH) memory data is input for error detection and correction. Data is output on the Memory Data Bus, when $\overline{MOE}$ is LOW.
CBI_{0-7}	I	**Check Bit Inputs:** interface to the check bit memory.
$CBSYN_{0-7}$	O	**Check Bit/Syndrome Output:** When $\overline{MOE}$ is LOW the generated check bits are output. When CBSEL is HIGH and $\overline{MOE}$ is HIGH, the syndrome bits are output. The bus is tristated when $\overline{MOE}$ = 1 and CBSEL = 0.
P_{0-7}	I/O	**Parity for bytes 0 to 7:** These pins are parity inputs when the corresponding Byte Enable (BE) is LOW or $\overline{SOE}$ is HIGH, and are used to generate the parity error signal ($\overline{PERR}$). These pins are outputs when the corresponding Byte Enable (BE) is HIGH and $\overline{SOE}$ is LOW.
Control Inputs		
$\overline{SOE}$	I	**System Output Enable:** enables system data bus output drivers if the corresponding Byte Enable (BE_{0-7}) is HIGH.
BE_{0-7}	I	**Byte Enable:** is used along with $\overline{SOE}$, to enable the System Data outputs for a particular byte. For example, if BE_1 is HIGH, the System data outputs for byte 1 (SD_{8-15}) are enabled. The BE_{0-7} pins also control the byte mux. If a particular BE is HIGH during a memory read cycle, that byte is fed back to the memory data bus. This is used during partial word write operations and writing corrected data back to memory.
$\overline{MOE}$	I	**Memory Output Enable:** when LOW, enables the output buffers of the memory data bus (MD) and CBSYN bus. It also controls the CBSYN mux. When LOW, checkbits are selected, when HIGH, syndrome is selected.
MDILE	I	**Memory Data Input Latch Enable:** on the HIGH-to-LOW transition, latches MD and CBI in MD input latch and MD check bit latch respectively. The latches are transparent when MDILE is HIGH.
$\overline{MDOLE}$	I	**Memory Data Output Latch Enable:** latches data in the MD output latch on the LOW-to-HIGH transition of $\overline{MDOLE}$. When $\overline{MDOLE}$ is LOW, the MD output latch is transparent.
$\overline{SDOLE}$	I	**System Data Output Latch Enable:** latches data in the SD output latch and the SD checkbit latch on the LOW-to-HIGH transition of $\overline{SDOLE}$. The latch is transparent when $\overline{SDOLE}$ is LOW.
SDILE	I	**System Data Input Latch Enable:** latches SD in the SD input latch on the HIGH-to-LOW transition. When SDILE is HIGH, the SD input latch is transparent.
WBSEL	I	**Write FIFO Select:** when HIGH, the write FIFO is selected. When WBSEL is LOW, the SD input latch is selected.
$\overline{WBEN}$	I	**Write FIFO Enable:** when LOW, allows SD data to be written to the write FIFO on the SCLK rising edge.
$\overline{WBREN}$	I	**Write FIFO Read Enable:** when LOW, allows data to be read from the the write FIFO on MCLK rising edge.
RS_{0-1}	I	**Reset and Select pins** (read and write FIFO FIFOs) RS_1 RS_0 Function 0 0 Reset 16-deep FIFO or first 8-deep FIFO 0 1 Reset second 8-deep FIFO 1 0 Select 16-deep FIFO or first 8-deep FIFO 1 1 Select second 8-deep FIFO

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PIN DESCRIPTION (Continued)

Pin Name	I/O	Description
RBSEL	I	**Read FIFO Select:** when HIGH, read FIFO is selected (data goes through read FIFO, not MD output latch). When LOW, the MD output latch is selected.
$\overline{\text{RBEN}}$	I	**Read FIFO Enable:** when LOW, allows data to be written into the read FIFO on the LOW-to-HIGH transition of the memory clock.
$\overline{\text{RBREN}}$	I	**Read FIFO Enable:** when LOW, allows data to be read from the read FIFO on the LOW-to-HIGH transition of SCLK
$\overline{\text{CBSEL}}$	I	**Checkbit Syndrome Output Enable:** Controls the CBSYN output buffer.When HIGH, the buffer is enabled. When CBSEL is LOW, $\overline{\text{MOE}}$ controls the buffer.
$\overline{\text{MEN}}$	I	**Mode Enable Input:** when LOW, $SD_{0\text{-}15}$ is loaded into the EDC mode register on the LOW-to-HIGH transition of the SCLK. This pin must be held LOW for the entire SCLK HIGH period, as shown in Figure 4.
Clock Inputs		
MCLK	I	**Memory Clock:** on the LOW-to-HIGH transition of MCLK, memory data is written to the read FIFO when $\overline{\text{RBEN}}$ is LOW. Data is read from the write FIFO when $\overline{\text{WBREN}}$ is LOW, on the LOW-to-HIGH transition of MCLK.
SCLK	I	**System Clock:** on the LOW-to-HIGH transition of the SCLK, data is read from the read FIFO when $\overline{\text{RBREN}}$ is LOW. Data on the system data bus is written into the write FIFO when $\overline{\text{WBEN}}$ is LOW on the LOW-to-HIGH transition of SCLK. Clocks data into mode register when $\overline{\text{MEN}}$ is LOW.
SYNCLK	I	**Syndrome Clock:** Used to load diagnostic registers. When an error occurs, Error Counter is incremented on the rising SYNCLK edge (up to 15 errors). On the first error after a diagnostic reset, SYNCLK rising edge clocks data into Check Bit, Syndrome, Error Type and Error Data registers. One of the syndrome registers has new data clocked in on every SYNCLK rising edge.
Status Outputs		
$\overline{\text{WBEF}}$	O	**Write FIFO Empty Flag:** when LOW, indicates that the write FIFO is empty. After a reset, the $\overline{\text{WBEF}}$ goes LOW.
$\overline{\text{WBFF}}$	O	**Write FIFO Full Flag:** when LOW, indicates that the write FIFO is full. After a reset, $\overline{\text{WBFF}}$ goes HIGH.
$\overline{\text{RBEF}}$	O	**Read FIFO Empty Flag:** when LOW, indicates that the read FIFO is empty. After a reset, the $\overline{\text{RBEF}}$ goes LOW.
$\overline{\text{RBHF}}$	O	**Read FIFO Half-full Flag:** when LOW, indicates that there are eight or more data words (in the 16-deep configuration) or four or more data words (in the dual 8-deep configuration) in the read FIFO. The flag will return HIGH when less than eight (or four) data words are in the FIFO.
$\overline{\text{RBFF}}$	O	**Read FIFO Full Flag:** when LOW, indicates that the read FIFO is full. After a reset, $\overline{\text{RBFF}}$ goes HIGH.
$\overline{\text{ERR}}$	O	**Error Flag:** when $\overline{\text{ERR}}$ is LOW, a data error is indicated. The $\overline{\text{ERR}}$ is not latched internally.
$\overline{\text{MERR}}$	O	**Multiple Error Flag:** when $\overline{\text{MERR}}$ is LOW, a multiple data error is indicated. The $\overline{\text{MERR}}$ is not latched internally.
$\overline{\text{PERR}}$	O	**Parity Error Flag:** when LOW, indicates a parity error on the system data bus input.
Power Supply		
V_{CC}	P	Power Supply Voltage.
GND	P	Ground.

3268 tbl 02

DETAILED DESCRIPTION —

64-BIT MODIFIED HAMMING CODE - CHECKBIT ENCODING CHART(1, 2)

Generated Checkbits	Parity	Participating Data Bits															
		0	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15
CB0	Even (XOR)		X	X	X		X			X	X		X			X	
CB1	Even (XOR)	X	X	X		X		X		X		X		X			
CB2	Odd (XNOR)	X			X	X			X		X	X			X		X
CB3	Odd (XNOR)	X	X				X	X	X				X	X	X		
CB4	Even (XOR)			X	X	X	X	X	X							X	X
CB5	Even (XOR)									X	X	X	X	X	X	X	X
CB6	Even (XOR)	X	X	X	X	X	X	X	X								
CB7	Even (XOR)	X	X	X	X	X	X	X	X								

3268 tbl 03

Generated Checkbits	Parity	Participating Data Bits															
		16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31
CB0	Even (XOR)		X	X	X		X			X	X		X			X	
CB1	Even (XOR)	X	X	X		X		X		X		X		X			
CB2	Odd (XNOR)	X			X	X			X		X	X			X		X
CB3	Odd (XNOR)	X	X				X	X	X				X	X	X		
CB4	Even (XOR)			X	X	X	X	X	X							X	X
CB5	Even (XOR)									X	X	X	X	X	X	X	X
CB6	Even (XOR)									X	X	X	X	X	X	X	X
CB7	Even (XOR)									X	X	X	X	X	X	X	X

3268 tbl 04

Generated Checkbits	Parity	Participating Data Bits															
		32	33	34	35	36	37	38	39	40	41	42	43	44	45	46	47
CB0	Even (XOR)	X				X		X	X			X		X	X		X
CB1	Even (XOR)	X	X	X		X		X		X		X		X			
CB2	Odd (XNOR)	X			X	X			X		X	X			X		X
CB3	Odd (XNOR)	X	X				X	X	X				X	X	X		
CB4	Even (XOR)			X	X	X	X	X	X							X	X
CB5	Even (XOR)									X	X	X	X	X	X	X	X
CB6	Even (XOR)	X	X	X	X	X	X	X	X								
CB7	Even (XOR)									X	X	X	X	X	X	X	X

3268 tbl 05

Generated Checkbits	Parity	Participating Data Bits															
		48	49	50	51	52	53	54	55	56	57	58	59	60	61	62	63
CB0	Even (XOR)	X				X		X	X			X		X	X		X
CB1	Even (XOR)	X	X	X		X		X		X		X		X			
CB2	Odd (XNOR)	X			X	X			X		X	X			X		X
CB3	Odd (XNOR)	X	X				X	X	X				X	X	X		
CB4	Even (XOR)			X	X	X	X	X	X							X	X
CB5	Even (XOR)									X	X	X	X	X	X	X	X
CB6	Even (XOR)									X	X	X	X	X	X	X	X
CB7	Even (XOR)	X	X	X	X	X	X	X	X								

3268 tbl 06

NOTES:

1. The table indicates the data bits participating in the checkbit generation. For example, checkbit CB0 is the Exclusive-OR function of the 64 data input bits marked with an X.
2. The checkbit is generated as either an XOR or an XNOR of the 64 data bits noted by an “X” in the table.

DETAILED DESCRIPTION —

64-BIT SYNDROME DECODE TO BIT-IN-ERROR(1)

					HEX	0	1	2	3	4	5	6	7	8	9	A	B	C	D	E	F
					S7	0	0	0	0	0	0	0	0	1	1	1	1	1	1	1	1
					S6	0	0	0	0	1	1	1	1	0	0	0	0	1	1	1	1
			Syndrome		S5	0	0	1	1	0	0	1	1	0	0	1	1	0	0	1	1
			Bits		S4	0	1	0	1	0	1	0	1	0	1	0	1	0	1	0	1
HEX	S3	S2	S1	S0																	
0	0	0	0	0		*	C4	C5	T	C6	T	T	62	C7	T	T	46	T	M	M	T
1	0	0	0	1		C0	T	T	14	T	M	M	T	T	M	M	T	M	T	T	30
2	0	0	1	0		C1	T	T	M	T	34	56	T	T	50	40	T	M	T	T	M
3	0	0	1	1		T	18	8	T	M	T	T	M	M	T	T	M	T	2	24	T
4	0	1	0	0		C2	T	T	15	T	35	57	T	T	51	41	T	M	T	T	31
5	0	1	0	1		T	19	9	T	M	T	T	63	M	T	T	47	T	3	25	T
6	0	1	1	0		T	20	10	T	M	T	T	M	M	T	T	M	T	4	26	T
7	0	1	1	1		M	T	T	M	T	36	58	T	T	52	42	T	M	T	T	M
8	1	0	0	0		C3	T	T	M	T	37	59	T	T	53	43	T	M	T	T	M
9	1	0	0	1		T	21	11	T	M	T	T	M	M	T	T	M	T	5	27	T
A	1	0	1	0		T	22	12	T	33	T	T	M	49	T	T	M	T	6	28	T
B	1	0	1	1		17	T	T	M	T	38	60	T	T	54	44	T	1	T	T	M
C	1	1	0	0		T	23	13	T	M	T	T	M	M	T	T	M	T	7	29	T
D	1	1	0	1		M	T	T	M	T	39	61	T	T	55	45	T	M	T	T	M
E	1	1	1	0		16	T	T	M	T	M	M	T	T	M	M	T	0	T	T	M
F	1	1	1	1		T	M	M	T	32	T	T	M	48	T	T	M	T	M	M	T

NOTES: 3268 tbl 07

1. The table indicates the decoding of the eight syndrome bits to identify the bit-in-error for a single-bit error, or whether a double or triple-bit error was detected. The all-zero case indicates no error detected.
   * = No errors detected
   # = The number of the single data bit-in-error
   T = Two errors detected
   M = Three or more detected
   C# = The number of the single checkbits in error

IDT49C3466 OPERATION

The EDC is involved in two types of operation — memory reads and memory writes. With the IDT49C3466, both these can be accomplished by utilizing either of two possible data paths — one incorporating the FIFO and the other without the FIFO. These operations are treated separately below.

Memory Write

The involvement of the EDC in this type of operation is relatively minimal since it does not call for any error checking. It only generates the check bits associated with each 64-bit wide data word. The EDC can be in generate-detect or normal mode for this operation.

When a write operation is performed, it must be ensured that the SD output buffer (enabled by $\overline{SOE}$ and BE_{0-7}) is disabled so that no attempt is made to simultaneously transfer read data onto the System Data (SD) Bus.

When the write FIFO (WFIFO) is bypassed (WBSEL LOW), data passes through the SD Latch In. To latch data, the SDILE signal should be pulled LOW. The special case of a partial word write or byte merge is discussed later. Here it is assumed that all 64 bits are being written. Consequently, BE_{0-7} must all be LOW.

The data is fed to the SD Checkbit generator where appropriate checkbits are generated. Both system data and the generated checkbits can be latched by pulling the $\overline{SDOLE}$ signal HIGH. Asserting $\overline{MOE}$ enables the MD output buffer and data is output to the Memory Data (MD) bus. $\overline{CBSEL}$ (=1) or $\overline{MOE}$(=0) need to be asserted to enable the CBSYN output buffer and output checkbits on $CBSYN_{0-7}$.

When the write FIFO is selected (WBSEL = 1), instead of asserting SDILE, $\overline{WBEN}$ is asserted and data is clocked into the write FIFO on the rising edge of SCLK. $\overline{WBFF}$ is asserted when the WFIFO is full and this inhibits further write attempts (see section on "Clock Skew" and "R/W FIFO Operation at Boundaries") to the WFIFO. When $\overline{WBREN}$ is asserted, data can be clocked out of the write FIFO on the rising edge of MCLK. $\overline{WBEF}$ is asserted when the WFIFO is empty and this inhibits further read attempts (see section on "Clock Skew") from the WFIFO.

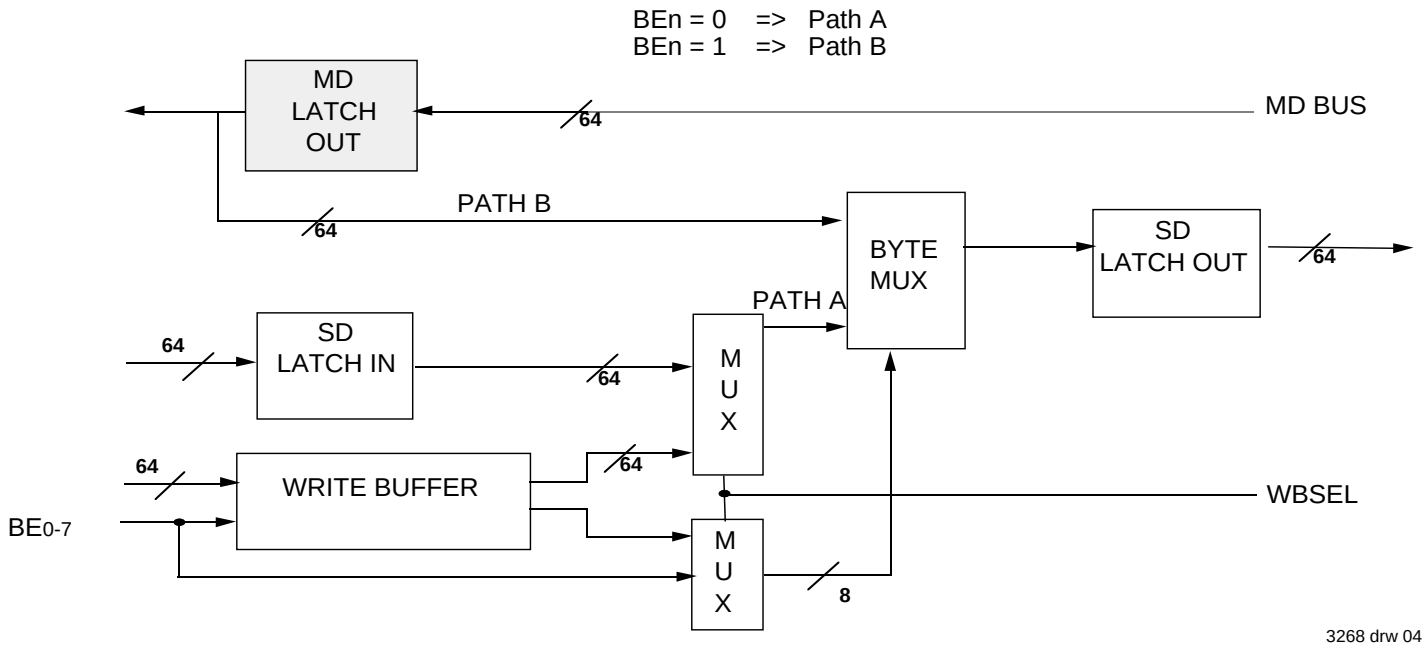


Figure 1. Byte Merge

Memory Read

During a memory read, data and the corresponding input checkbits are read from the MD bus and CBI0-7, respectively. The memory and checkbit data may both be latched as they come in (MD Latch In and MD Checkbit latch) by the MDILE signal. Memory data is sent to the MD checkbit generator (where checkbits corresponding to the input data are generated) and to the error correct circuitry. The generated checkbits are X-ORed with the input checkbits to produce the syndrome word. This is sent to the error correction circuitry which generates the corrected data (normal mode). The corrected data is output to the SD bus via either of two data paths. When RBSEL is LOW, data flows through MD Latch Out. Pulling MDOLE HIGH latches this data. The output buffer is enabled by asserting SOE (=0) and BE0-7 (=1). Corrected data can be written back to memory by enabling the MD output buffer. In order to ensure selection of the write back path (Path B in figure 1) at the byte mux, BEO-7 should be all 1's while WBSEL = 0. If WBSEL = 1, buffered BEO-7 from the output of the write FIFO controls the byte mux.

If the read FIFO (RFIFO) is selected (RBSEL HIGH), data is clocked into the FIFO (Read_FIFO Write) when RBEN is LOW, on the rising edge of MCLK. RBFF is asserted when the RFIFO is full and this inhibits further write attempts to the RFIFO (see section on "Clock Skew" and "R/W FIFO operation at Boundaries"). Data is clocked out of the FIFO (Read_FIFO Read) when RBREN is LOW on the rising edge of SCLK. RBEF is asserted when the RFIFO is empty and this inhibits further read attempts (see section on "Clock Skew") from the RFIFO.

Note: In case of multiple error SD should be ignored in correct mode.

Clock Skew

A skew between the read and write clocks, as specified by tskew, is recommended. This specification is not a stringent one, in the manner of setup and hold times, but is important in preempting latencies at FIFO boundaries. For example – When a word is written to an empty FIFO, there is a finite delay before the FIFO is recognized as no longer being empty and hence allowing a read from the same FIFO. Similarly when a word is read from a full FIFO, there is a delay before a write can successfully be attempted. The tskew specification accounts for these cases. During cycles other than on full/empty FIFO boundaries, the clock skew is not required and the device functions correctly even when the reads and writes occur simultaneously. If the tskew specification is ignored and SCLK and MCLK were permanently tied together, there is an extra cycle latency in the cases mentioned above. Clock skew violation is illustrated in Figure 13.

FIFO Write Latency

The first data written to either of the (read or write) FIFOs, after the FIFO is reset, suffers a single clock latency. Data that is set-up with respect to the first clock is ignored and the data that is set-up with respect to the second clock edge after the reset, is stored as the first data in the FIFO (Refer to Figures 9 and 10). The empty-flag is deasserted after this second clock edge and 15 more data words (in a 16 deep configuration) can be written to the FIFO after this.

The latency can be reduced or eliminated by providing a "dummy" or "set-up" clock edge before the actual write to the FIFO. The dummy write clock can be provided any time after reset and before the next buffer write operation takes place. The latency described here (shown in Figures 10 and 13) occurs only after a FIFO reset. In other cases where the FIFO becomes empty there is no latency.

R/W FIFO Operation At Boundaries

In the 49C3466 the write pointer is incremented on every FIFO write. Similarly the read pointer is incremented on every FIFO read. In most cases on a FIFO read, the last data read remains at the output of the FIFO, until the read pointer is further incremented. On the last (the write that fills the FIFO) FIFO write after the FIFO read, however, this last read data is overwritten by the 16th write following the empty condition and consequently the data at the FIFO output is liable to change. The situation is depicted in the diagram below.

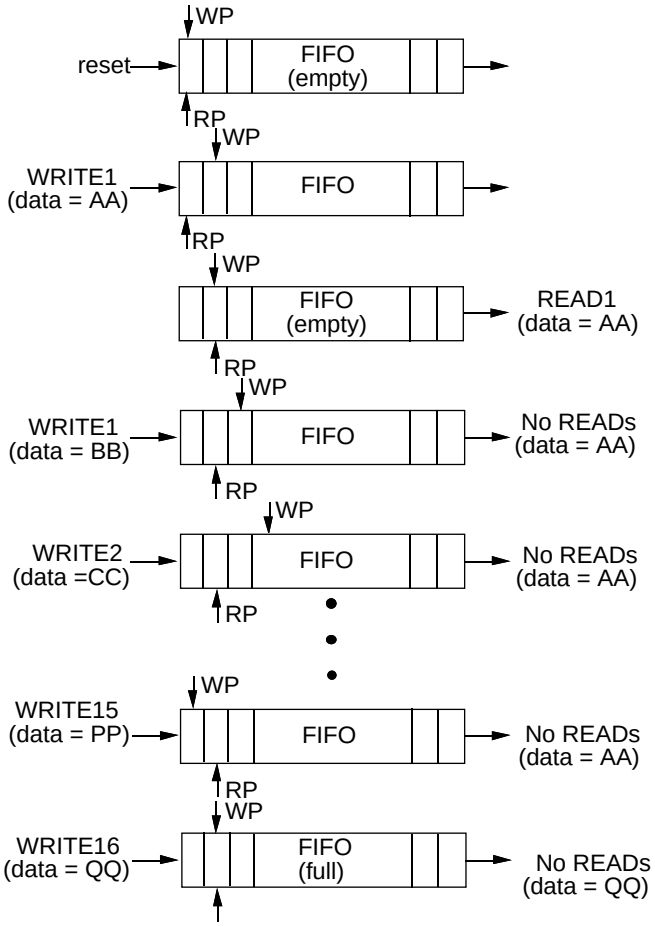


Figure 2. R/W FIFO Operation

The diagram in figure 2 progresses from the FIFO initialization(reset) through a sequence of write operations. After the first write, a read is executed which establishes the data at the FIFO output(AA). On the last write to the FIFO(the write that fills the FIFO), the location of the last read data is overwritten and the FIFO output changes from AA to the data just written, namely QQ.

This operation needs to be taken into account in the design of the system. In case of a burst operation where FIFO data is output at a much slower rate than the rate at which data is input and the full flag is expected to inhibit further writes, the user cannot expect the FIFO output to remain static through the 16th write of the burst. If this is a requisite to the design, the FIFO output should be latched. In the case of the write FIFO this can be accomplished on-chip by latching the FIFO output in the SD output latch. For the read FIFO, the FIFO output must be latched externally to accomplish the same thing, since there is no latch on-chip following the FIFO. If this cannot be done and the situation described above is expected to occur in normal operation, the write must be inhibited one cycle before the FIFO becomes full.

Partial Word Write/Byte Merge

Writing a word shorter than 64 bits to memory is treated as a special case. The checkbits generated for a data word shorter than 64 bits and written to a particular memory location differ from the checkbits that would be generated by the entire 64-bit data word at the same location. Hence, the byte merge operation requires reading of the contents of the memory location to be written to, merging the byte/bytes being written (from SD side) with the other component bytes previously at that memory location (from MD side), generating a checkbit word for this composite word and writing both the composite data word and the generated checkbits to memory. The BEn bits supplied by the user determine the bytes that come from SD and those that come from MD, as illustrated in Figure 1.

EDC Modes

The IDT49C3466 has 5 modes of operation. Refer to table below for a description of the modes.

The **Error Data Output** mode is useful for memory initialization as described below. In **Checkbit Injection mode**, the MD Checkbit Latch is loaded with data from the System Bus. This serves to verify the functioning of the EDC. Any discrepancy between the injected checkbits and generated checkbits should result in assertion of the $\overline{ERR}$, $\overline{MERR}$ signals.

These modes and certain other features such as clear, buffer configuration, etc., can be selected by appropriately loading the Mode Register. The Mode Register can be written to by asserting $\overline{MEN}$. Then SD_{0-15} is clocked into the mode register on the rising edge of SCLK.

MODE REGISTER CONFIGURATION

15 7	6	5	4	3	2 0
UNUSED	RMODE	PSEL	RWBD	CLEAR	EDCM0-2

EDCM2	EDCM1	EDCM0	OPERATION
0	0	0	ERROR-DATA OUTPUT MODE
0	0	1	DIAGNOSTIC-OUTPUT MODE
0	1	0	GENERATE-DETECT MODE
0	1	1	NORMAL MODE
1	0	0	CHECKBIT-INJECTION MODE

RMODE	OPERATION
0	NOP
1	READ MODE REGISTER ON SD BUS

RWBD	OPERATION
0	DUAL FIFOS (8)
1	SINGLE FIFO (16)

CLEAR	OPERATION
0	NOP
1	CLEAR ALL DIAGNOSTIC REGISTERS

PSEL	OPERATION
0	EVEN PARITY
1	ODD PARITY

3268drw 05

OPERATING MODE DESCRIPTION

Mode	Description
MODE 0	**Error-Data Output Mode:** This mode allows the uncorrected data captured from an error event by the Error-Data Register to be read by the system for diagnostic purposes. The Error-Data Register is cleared by setting the mode register "'clear"-bit.
MODE 1	**Diagnostic-Output Mode:** In this mode, contents of latch and five internal registers are read by the system for diagnostic and error logging purposes. Internal data paths allow output from the CBI LATCH to be read directly by the system bus for diagnostic purposes. The contents of the internal diagnostic checkbit register, syndrome registers, error count register and error-type register are also output on the SD bus.
MODE 2	**Generate-Detect Mode:** (Detect-Only) The EDC performs checkbit generation during a memory write, and performs error detection only during a memory read.
MODE 3	**Normal Mode:** The EDC performs checkbit generation during memory writes and error detection and correction during memory reads.
MODE 4	**Checkbit-Injection Mode:** In this mode, the checkbit latch is loaded with desired 8-bit data from the SD bus.This eight bit data passes through SD Latch in or write FIFO to the MD check bit latch. By inserting various checkbit values, correct functioning of the EDC can be verified “on-board”. The rest of the operation is similar to regular memory reads. The EDC compares the injected checkbits against the internally generated checkbits. Any discrepancy in the injected checkbits and the internally generated checkbits will cause the $\overline{ERR}$ / $\overline{MERR}$ to go LOW.

3268 tbl 08

Memory Initialization

Memory initialization involves clearing all memory data locations and writing the corresponding checkbits (checkbits corresponding to all zero data = $0C) to checkbit memory. This can be done using the 49C3466 to first create an "all-zero-data" source. This is done by setting the CLEAR bit in the mode register. This clears all diagnostic registers. Then this data can be written back to memory in the Error-Data output (Mode 0) mode. In order to wrap the all-zero data back to the MD bus, BE0-7 should be high and WBSEL =0.

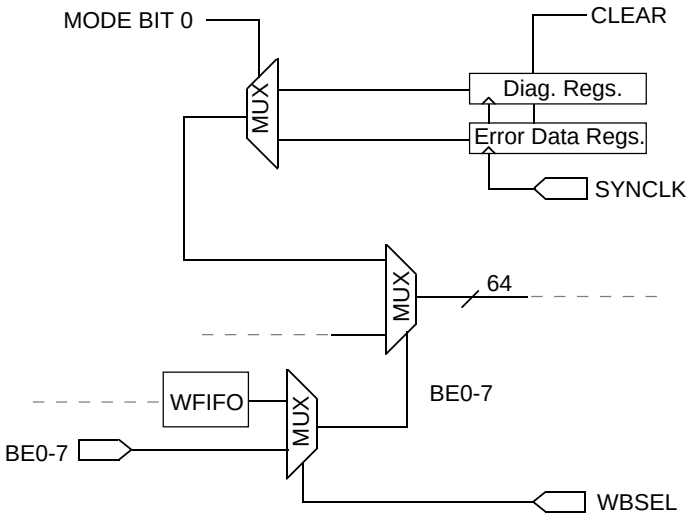
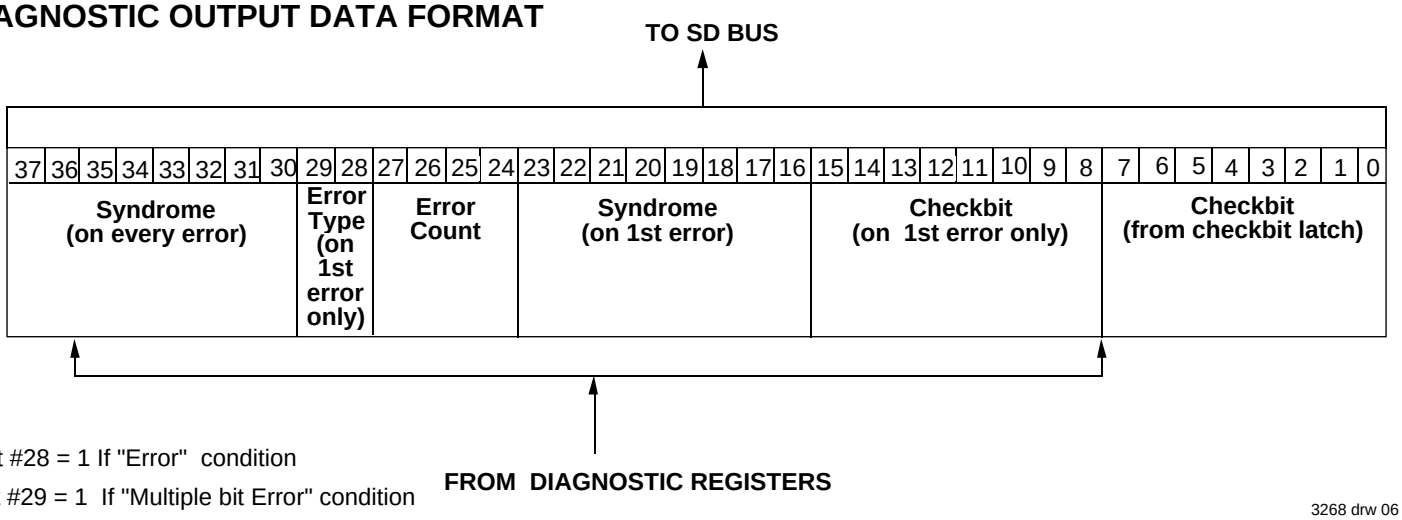


Fig 3. Memory Initialization using Diagnostic Output/Error Data Output Mode

DIAGNOSTIC OUTPUT DATA FORMAT



* Bit #28 = 1 If "Error" condition
Bit #29 = 1 If "Multiple bit Error" condition

3268 drw 06

Diagnostics

The diagnostic ability of the IDT49C3466 rests on a set of 6 registers that provide error logging information. These include the checkbit register, error count register, error type register, 2 syndrome registers and the error data register. Data is clocked into each of these registers by SYNCLK. The error data register, checkbit register, error type register and one of the syndrome registers are reloaded only in the case of the first error after a clear. The other syndrome register and the error count register are reloaded on every error condition SYNCLK edge. The contents of the Error Data register can be read only in Error Data Output mode. The contents of the other diagnostic registers as well as the checkbit latch can be read in Diagnostic Output mode.

Parity

The IDT49C3466 provides a parity check and generation facility. On a memory read the EDC generates parity bits for each data byte and outputs the parity byte on the parity bus, P0-7. During a memory write, parity is checked by comparing the parity bits input on P0-7 and the parity bits generated from the input data word. A discrepancy between these two causes the $\overline{PERR}$ flag to be asserted. In the case of partial word writes, the $\overline{PERR}$ flag is based on the parity bits Px and data bytes input on SD bus.

DIAG. REGISTER	LOADED BY	CONDITION	OUTPUT
CHECKBIT	SYNCLK ↑	ONLY ON 1st ERROR	SD8-15
SYNDROME (On 1st ERR)	SYNCLK ↑	ONLY ON 1st ERROR	SD16-23
ERR CNT	SYNCLK ↑	ON EVERY ERROR (Up to 15 ERRORS)	SD24-27
ERR TYPE	SYNCLK ↑	ONLY ON 1st ERROR	SD28-29
SYNDROME (On every ERROR)	SYNCLK ↑	ON EVERY ERROR	SD30-37

ABSOLUTE MAXIMUM RATINGS(1)

Symbol	Rating	Commercial	Unit
V_{TERM}(2)	Terminal Voltage with Respect to GND	–0.5 to +4.6	V
V_{TERM}(3)	Terminal Voltage with Respect to GND	–0.5 to +4.6	V
V_{TERM}(4)	Terminal Voltage with Respect to GND	–0.5 to V_{CC} + 0.5	V
T_{STG}	Storage Temperature	–65 to +150	°C
I_{OUT}	DC Output Current	30	mA

3268 tbl 09

NOTES:
1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
2. Vcc terminals.
3. Input terminals.
4. Output and I/O terminals.

CAPACITANCE (T_A = +25°C, f = 1.0 MHz)

Symbol	Parameter(1)	Conditions	Typ.	Unit
C_{IN}	Input Capacitance	V_{IN} = 0V	5	pF
C_{OUT}	Output Capacitance	V_{OUT} = 0V	7	pF

3268 tbl 10

NOTE:
1. This parameter is sampled and not 100% tested.

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

The following conditions apply unless otherwise specified:
Commercial: T_A = 0°C to +70°C, V_{CC} = 3.3V ±0.3V

Symbol	Parameter	Test Conditions[1]		Min.	Typ.[2]	Max.	Unit
V_{IH}	Input HIGH Level (Input pins)	Guaranteed Logic HIGH Level		2.0	—	3.6	V
	Input HIGH Level (I/O pins)			2.0	—	V_{CC}+0.5	
V_{IL}	Input LOW Level (Input and I/O pins)	Guaranteed Logic LOW Level		–0.5	—	0.8	V
I_{IH}	Input HIGH Current	V_{CC} = Max.	V_I = V_{CC}	—	—	±1	
I_{IL}	Input LOW Current		V_I = GND	—	—	±1	
I_{OZH}	High Impedance Output Current	V_{CC} = Max.	V_O = V_{CC}	—	—	±1	µA
I_{OZL}	(3-State Output pins)		V_O = GND	—	—	±1	
I_{OS}	Short Circuit Current[4]	V_{CC} = Max.[3] V_{OUT} = 0V			—		mA
V_{OH}	Output HIGH Voltage	V_{CC} = Min. V_{IN} = V_{IH} or V_{IL}	I_{OH} = –1mA	2.4[5]	3.0	—	V
V_{OL}	Output LOW Voltage	V_{CC} = Min. V_{IN} = V_{IH} or V_{IL}	I_{OL} = 4mA	—	0.3	0.5	V
V_H	Input Hysteresis on input control lines			—	100	—	mV

3268 tbl 11

NOTES:
1. For conditions shown as Max. or Min., use appropriate value specified under Electrical Characteristics for the applicable device type.
2. Typical values are at Vcc = 3.3V, +25°C ambient.
3. Not more than one output should be tested at one time. Duration of the test should not exceed one second.
4. This parameter is guaranteed but not tested.
5. V_{OH} = V_{CC} –0.6V at rated current.

POWER SUPPLY CHARACTERISTICS

The following conditions apply unless otherwise specified:
Commercial: T_A = 0°C to +70°C, V_{CC} = 3.3V ±0.3V

Symbol	Parameter	Test Conditions[1]	Min.	Typ.[2]	Max.	Unit
I_{CCQC}	Quiescent Power Supply Current	V_{IN} = V_{CC}, or V_{IN} = GND V_{CC} = Max.	—	3.0	15	mA
I_{CCQT}	Quiescent Power Supply Current TTL Input Levels	V_{IN} = V_{CC} –0.6 V_{CC} = Max.	—	1.5	100	µA/ Input
I_{CCD}	Dynamic Power Supply Current	V_{IN} = V_{CC}, or V_{IN} = GND V_{CC} = Max. f = 10MHz Correct Mode	—	—	—	mA

NOTES:
3268 tbl 12

1. For conditions shown as Min. or Max., use appropriate Vcc value.
2. Typical values are at V_{CC} = 3.3V, +25°C ambient temperature.

AC PARAMETERS
PROPAGATION DELAY TIMES

Number	Parameter	Description		Max.	Unit
		From Input(1)	To Output		
GENERATE (WRITE) PARAMETERS					
Without Write FIFO:					
1	t_{BC}	BEn	CBSYN (chkbit)	20	ns
2	t_{BM}	BEn	MDOUT	16	ns
3	t_{PPE}	Pxin	PERR	10	ns
4	t_{SC}	SDin	CBSYN (chkbit)	22	ns
5	**t_{SM}**	SDin	MDout	22	ns
6	t_{SPE}	SDin	$\overline{\text{PERR}}$	16	ns
With Write FIFO:					
7	t_{MC}	MCLK (Lo-Hi)	CBSYN (chkbit)	25	ns
8	t_{MMD}	MCLK (Lo-Hi)	MDout	25	ns
9	t_{WBSEL}	WBSEL	MDout	18	ns
DETECT (READ) PARAMETERS					
Without Read FIFO:					
10	t_{WYC}	SYNCLK (Lo-Hi)	CBSYN (syndr)	16	ns
11	**t_{ME}**	MDin	$\overline{\text{ERR}}$	20	ns
12	t_{MME}	MDin	$\overline{\text{MERR}}$	22	ns
13	t_{CE}	CBI	$\overline{\text{ERR}}$	13	ns
14	t_{CME}	CBI	$\overline{\text{MERR}}$	13	ns
With Read FIFO:					
15	t_{SSD}	SCLK (Lo-Hi)	SDout	22	ns
16	t_{RBSEL}	RBSEL	SDout	18	ns
CORRECT (READ) PARAMETERS					
Without Read FIFO:					
17	t_{CS}	CBI	SDout	20	ns
18	t_{MP}	MDin	Pxout	22	ns
19	**t_{MS}**	MDin	SDout	22	ns
With Read FIFO:					
20	t_{SP}	SCLK (Lo-Hi)	Pxout	22	ns

NOTE: 3268 tbl 13

* PRELIMINARY.
1. (Lo-Hi) indicates LOW-to-HIGH transition and vice versa.

PROPAGATION DELAY TIMES FROM LATCH ENABLES

Number	Parameter	Description		Max.	Unit
		From Input[1]	To Output		
21	t_{MLE}	MDILE (Lo-Hi)	$\overline{ERR}$	16	ns
22	t_{MLME}	MDILE (Lo-Hi)	$\overline{MERR}$	18	ns
23	t_{MLP}	MDILE (Lo-Hi)	Px (Detect Mode)	24	ns
24	t_{MLS}	MDILE (Lo-Hi)	SDout (Detect Mode)	22	ns
25	t_{MOLS}	$\overline{MDOLE}$ (Hi-Lo)	SDout	18	ns
26	t_{MOLP}	$\overline{MDOLE}$ (Hi-Lo)	Px	18	ns
27	t_{SLC}	SDILE (Lo-Hi)	CBSYN (chkbit)	20	ns
28	t_{SLM}	SDILE (Lo-Hi)	MDout	20	ns
29	t_{SOLC}	$\overline{SDOLE}$ (Hi-Lo)	CBSYN (chkbit)	12	ns
30	t_{SOLM}	$\overline{SDOLE}$ (Hi-Lo)	MDout	15	ns

NOTE:
3268 tbl 14

- PRELIMINARY.

1. (Lo-Hi) indicates LOW-to-HIGH transition and vice versa.

R/W FIFO TIMES

Number	Parameter	Description		Min.	Max.	Unit
		From Input[1]	To Output			
31	t_{RSF}	RS1 (Hi-Lo) during SCLK LOW	$\overline{EF}$ (Hi-Lo)/$\overline{FF}$ (Lo-Hi)	—	16	ns
32	t_{SKEW1}	RCLK (Lo-Hi) (SCLK or MCLK)	WCLK (Lo-Hi) (SCLK or MCLK)	10	—	ns
33	t_{SKEW2}	WCLK (Lo-Hi) (SCLK or MCLK)	RCLK (Lo-Hi) (SCLK or MCLK)	10	—	ns
34	t_{EF}	R/WCLK (Lo-Hi) (SCLK or MCLK)	$\overline{EF}$	—	15	ns
35	t_{FF}	R/WCLK (Lo-Hi) (SCLK or MCLK)	$\overline{FF}$	—	15	ns
39	t_{HFF}	R/WCLK (Lo-Hi) (SCLK or MCLK)	$\overline{HF}$	—	15	ns

NOTE:
3268 tbl 15

- PRELIMINARY.

1. (Lo-Hi) indicates LOW-to-HIGH transition and vice versa.

BYTE MERGE TIMES

Number	Parameter	Description		Max.	Unit
		From Input(1)	To Output		
36	t_{SCM}	SCLK (Lo-Hi)	MDout	25	ns
37	t_{MDM}	$\overline{\text{MDOLE}}$ (Hi-Lo)	MDout	18	ns
38	t_{RBM}	RBSEL	MDout	23	ns

3268 tbl 16

NOTE:
* PRELIMINARY.
1. (Lo-Hi) indicates LOW-to-HIGH transition and vice versa.

ENABLE AND DISABLE TIMES

Number	Parameter	Description				Min.	Max.	Unit
		From Input(1)		To Output				
40	t_{BESZx}	BEN =	High	SDout	*	—	22	ns
41	t_{BESxZ}		Low		Hi-Z	—	22	
42	t_{BEPZx}	BEN =	High	Pout	*	—	15	ns
43	t_{BEPxZ}		Low		Hi-Z	—	15	
44	t_{SEPZx}	$\overline{\text{SOE}}$ =	Low	Pout	*	—	14	ns
45	t_{SEPxZ}		High		Hi-Z	—	14	
46	t_{CECZx}	$\overline{\text{MOE}}$ =	Low	CBSYN	*	—	12	ns
47	t_{CECxZ}		High		Hi-Z	—	10	
48	t_{MEMZx}	$\overline{\text{MOE}}$ =	Low	MDout	*	—	22	ns
49	t_{MEMxZ}		High		Hi-Z	—	18	
50	t_{SESZx}	$\overline{\text{SOE}}$ =	Low	SDout	*	—	16	ns
51	t_{SESxZ}		High		Hi-Z	—	20	

3268 tbl 17

NOTES:
* PRELIMINARY.
1. (High-Z) indicates high impedence.
2. * indicates delay to both edges.

SET-UP AND HOLD TIMES

Number	Parameter	Description			Min.	Unit
		From Input(1)	To Output			
52	t_{CMLS}	CBI Set-up	before MDILE =	Hi-Lo	2	ns
53	t_{CMLH}	CBI Hold	after MDILE =	Hi-Lo	6	ns
54	t_{MMLS}	MDIN Set-up	before MDILE =	Hi-Lo	2	ns
55	t_{MMLH}	MDIN Hold	after MDILE =	Hi-Lo	6	ns
56	t_{CMOLS}	CBI Set-up (Correct)	before $\overline{\text{MDOLE}}$ =	Lo-Hi	10	1ns
57	t_{CMOLH}	CBI Hold (Correct)	after $\overline{\text{MDOLE}}$ =	Lo-Hi	2	ns
58a	t_{MMOLS}	MDIN Set-up (Detect)	before $\overline{\text{MDOLE}}$ =	Lo-Hi	10	ns
58b	t_{MMOLS}	MDIN Set-up (Correct)	before $\overline{\text{MDOLE}}$ =	Lo-Hi	10	ns
59a	t_{MMOLH}	MDIN Hold (Detect)	after $\overline{\text{MDOLE}}$ =	Lo-Hi	4	ns
59b	t_{MMOLH}	MDIN Hold (Correct)	after $\overline{\text{MDOLE}}$ =	Lo-Hi	4	ns
60	t_{MMCS}	MDIN Set-up	before MCLK =	Lo-Hi	10	ns
61	t_{MMCH}	MDIN Hold	after MCLK =	Lo-Hi	4	ns
62	t_{SSLS}	SDIN Set-up	before SDILE =	Hi-Lo	5	ns
63	t_{SSLH}	SDIN Hold	after SDILE =	Hi-Lo	3	ns
64	t_{SSCS}	SDIN Set-up	before SCLK	Lo-Hi	2	ns
65	t_{SSCH}	SDIN Hold	after SCLK	Lo-Hi	6	ns
66	t_{SSOLS}	SDIN Set-up	before $\overline{\text{SDOLE}}$ =	Lo-Hi	8	ns
67	t_{SSOLH}	SDIN Hold	after $\overline{\text{SDOLE}}$ =	Lo-Hi	0	ns
68	t_{SCSD}	SCLK (Lo-Hi)	before $\overline{\text{SDOLE}}$ =	Lo-Hi	14	ns
69	t_{MCSD}	MCLK (Lo-Hi)	before $\overline{\text{SDOLE}}$ =	Lo-Hi	14	ns
70	t_{ENS}	R/W FIFO Enable Set-up	before S/M CLK =	Lo-Hi	4	ns
71	t_{ENH}	R/W FIFO Enable Hold	after S/M CLK =	Lo-Hi	4	ns
72	t_{RSS}	RS1 (Lo-Hi)	R/WCLK =	Lo-Hi	6	ns
73	t_{MODS}	Mode Data Set-up	before SCLK =	Lo-Hi	4	ns
74	t_{MODH}	Mode Data Hold	after SCLK =	Lo-Hi	4	ns
75	t_{MENS}	Mode Enable Set-up	before SCLK =	Lo-Hi	4	ns
76	t_{MENH}	Mode Enable Hold	after SCLK =	Lo-Hi	4	ns
77	t_{MSDS}	MDIN Set-Up	before $\overline{\text{SDOLE}}$ =	Lo-Hi	22	ns
78	t_{MSDH}	MDIN Hold	after $\overline{\text{SDOLE}}$ =	Lo-Hi	0	ns
93	t_{BSCS}	BE Set-up	before SCLK =	Lo-Hi	1	ns
94	t_{BSCH}	BE Hold	after SCLK =	Lo-Hi	6	ns
DIAGNOSTIC SET-UP AND HOLD TIMES						
79	t_{CSCS}	CBI Set-up	before SYNCLK =	Lo-Hi	4	ns
80	t_{MSCS}	MDIN Set-up			10	ns
81	t_{MLSCS}	MDILE = Lo-Hi Set-up			10	ns
82	t_{CSCH}	CBI Hold	After SYNCLK=	Lo-Hi	6	ns
83	t_{MSCH}	MDIN Hold			6	ns
84	t_{MLSCH}	MDILE = Lo-Hi Hold			6	ns

NOTE:

3268 tbl 18

* PRELIMINARY.

1. (Lo-Hi) indicates LOW-to-HIGH transition and vice versa.

MINIMUM PULSE WIDTH

Number	Parameter	Description			Min.	Unit
		From Input[1]		Condition		
86	t_{RS}	Min. RS1 LOW time	to reset buffers	—	6	ns
87	t_{MLE}	Min. MDILE HIGH time	to strobe new data	MD, CBI = Valid	6	ns
88	t_{MDOLE}	Min. $\overline{\text{MDOLE}}$ LOW time	to strobe new data	—	6	ns
89	t_{SLE}	Min. SDILE HIGH time	to strobe new data	SD = Valid	6	ns
90	t_{CLK}	Min. S/MCLK HIGH time	to clock in new data	EN signal LOW	6	ns
91	t_{SYNCLK}	Min. SYNCLK HIGH time	to clock in new data	—	6	ns
92	t_{SDOLE}	Min. $\overline{\text{SDOLE}}$ LOW time	to clock in new data	—	6	ns

NOTE:

3268 tbl 19

* PRELIMINARY.

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	1V/ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	See Figure 15

2617 tbl 21

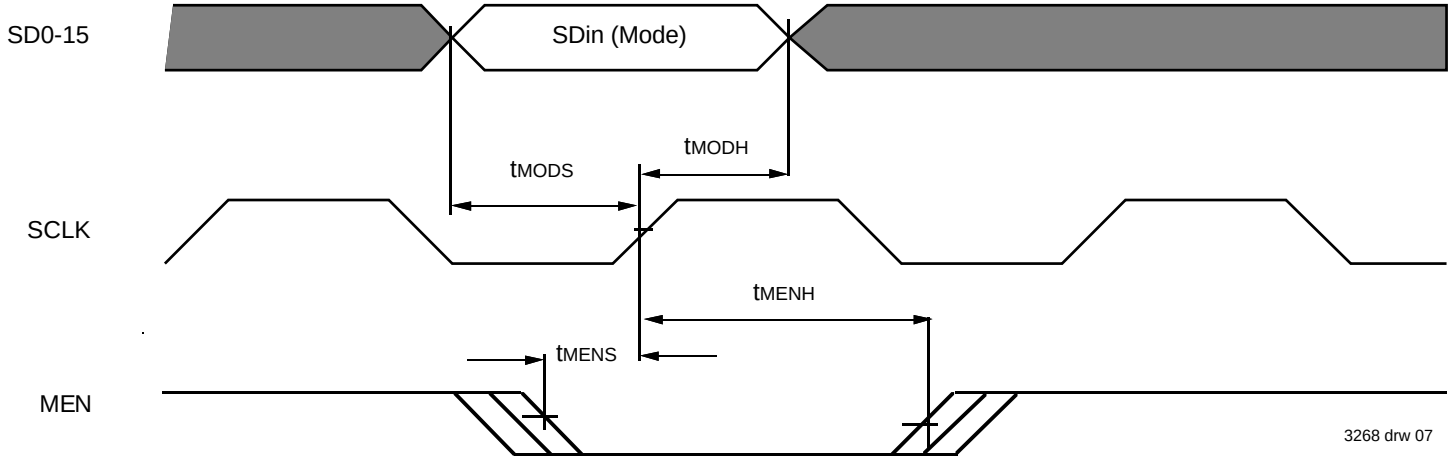


Figure 4. Mode Enable Timing

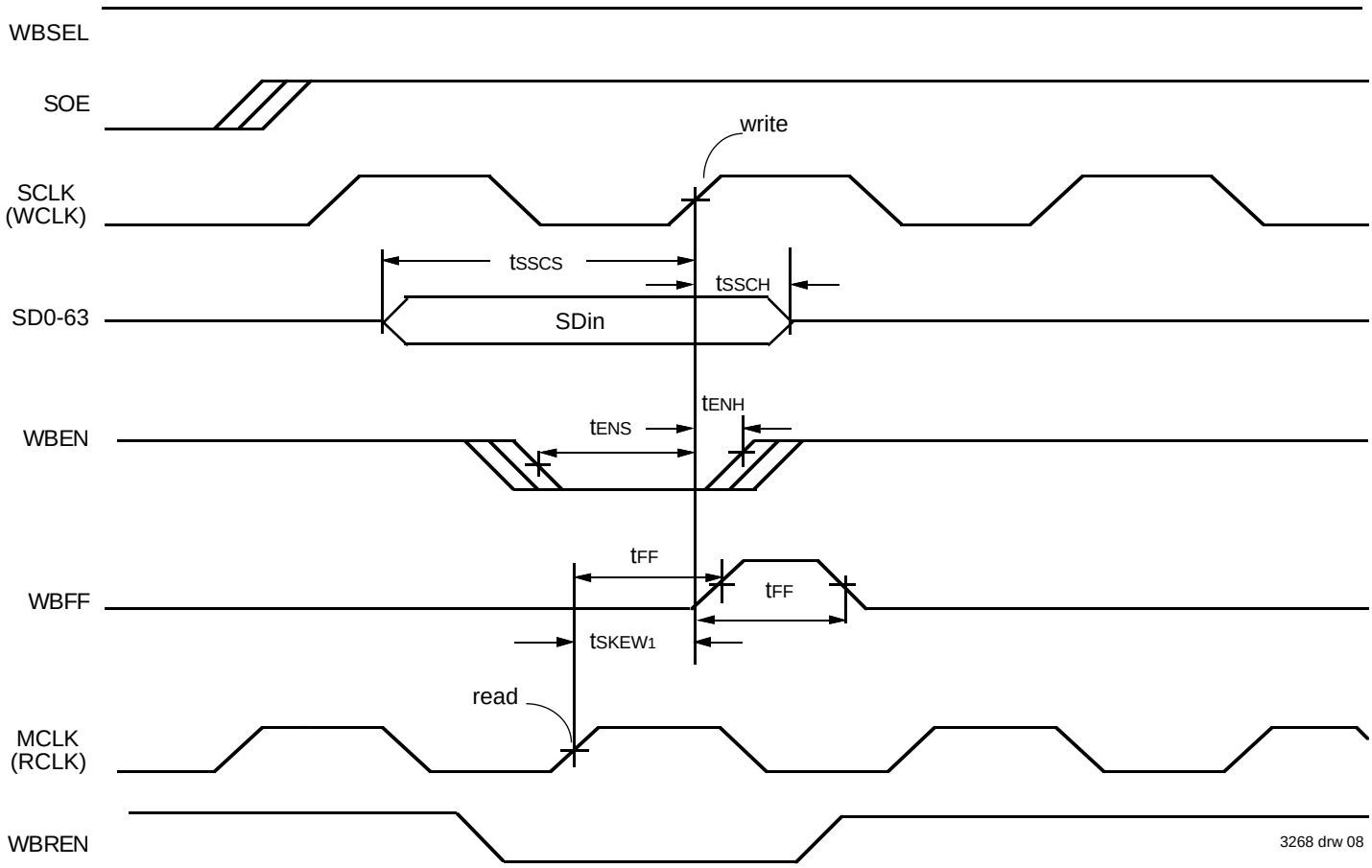


Figure 5. WFIFO Write Timing (Write Cycle)

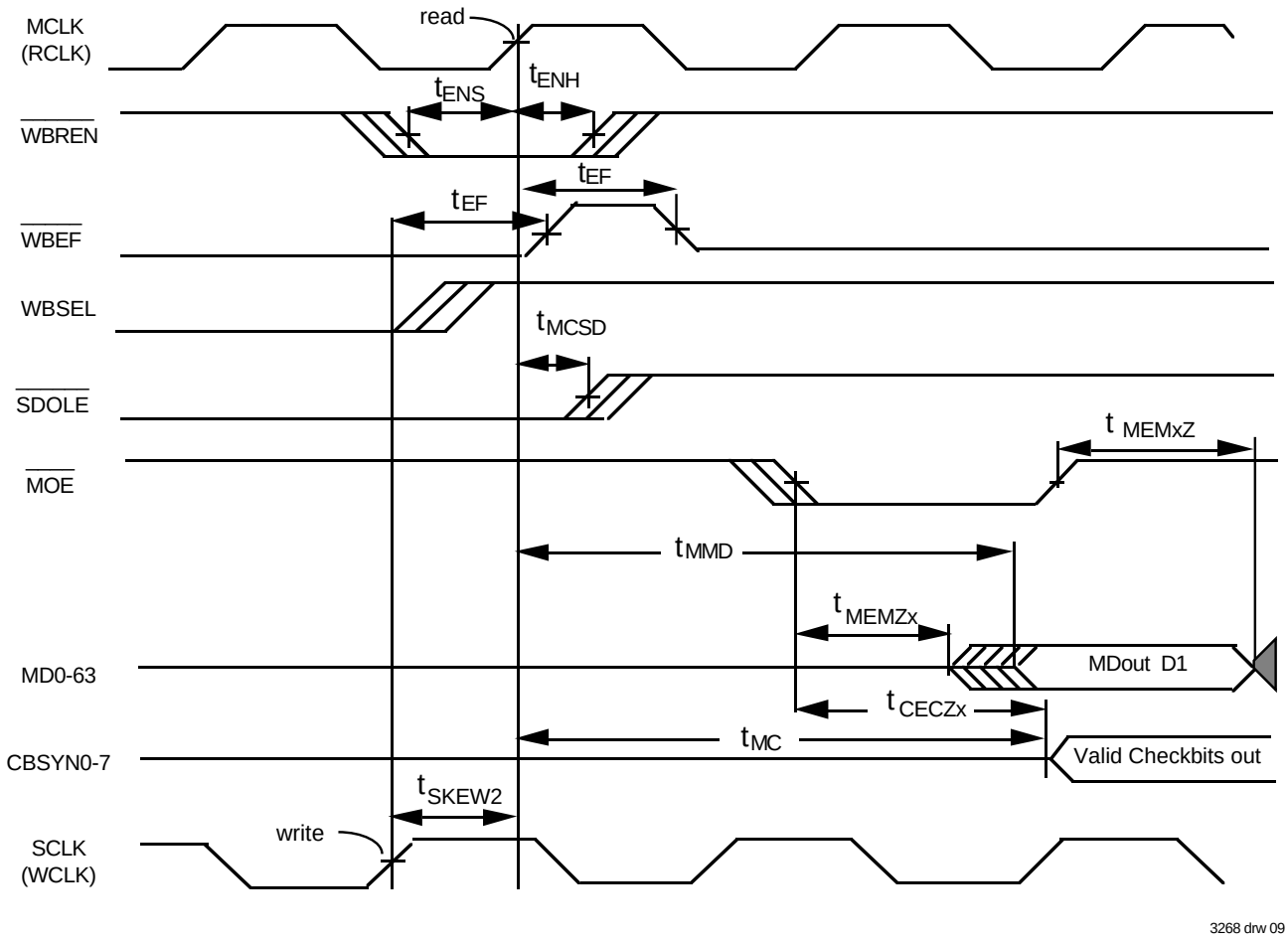


Figure 6. WFIFO Read and Checkbit Generate Timing (Write Cycle)

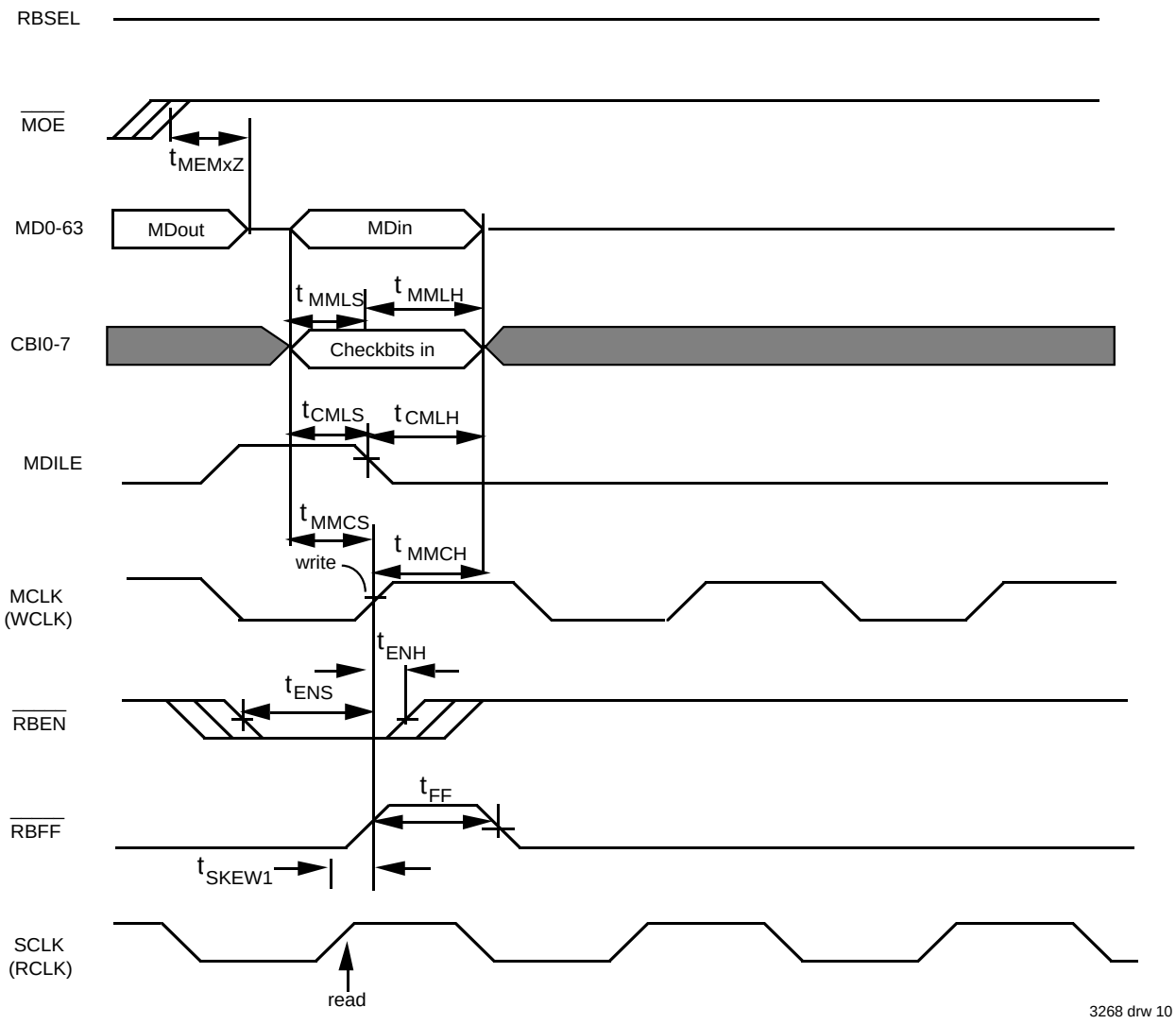


Figure 7. RFIFO Write Timing (Read Cycle)

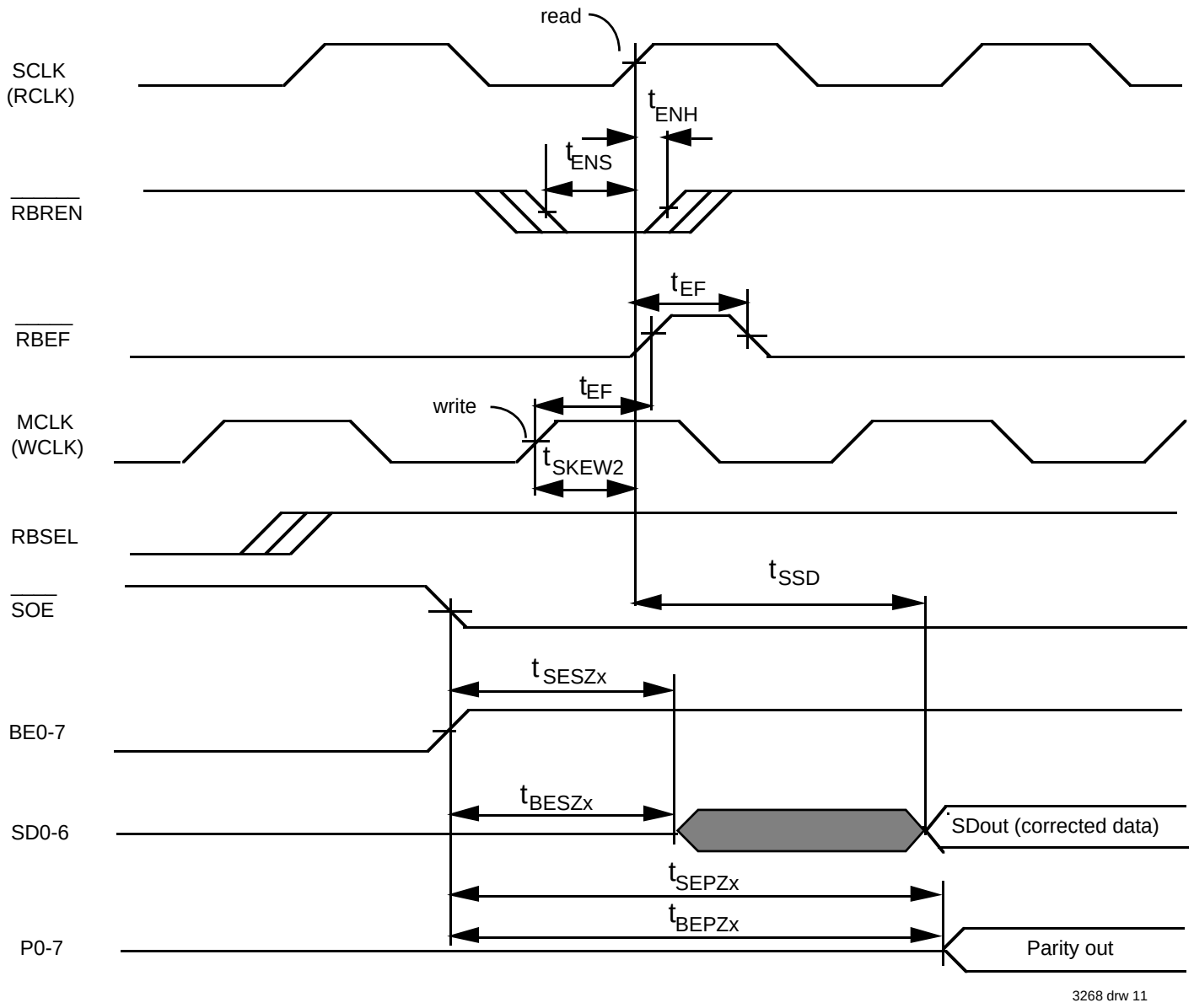


Figure 8. RFIFO Read Timing (Read Cycle)

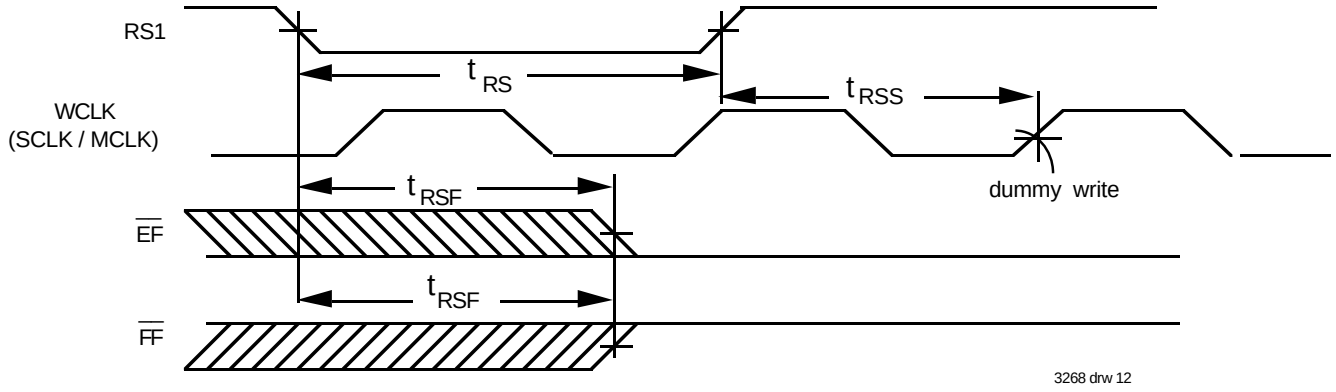


Figure 9. FIFO (WFIFO/RFIFO) Reset Timing

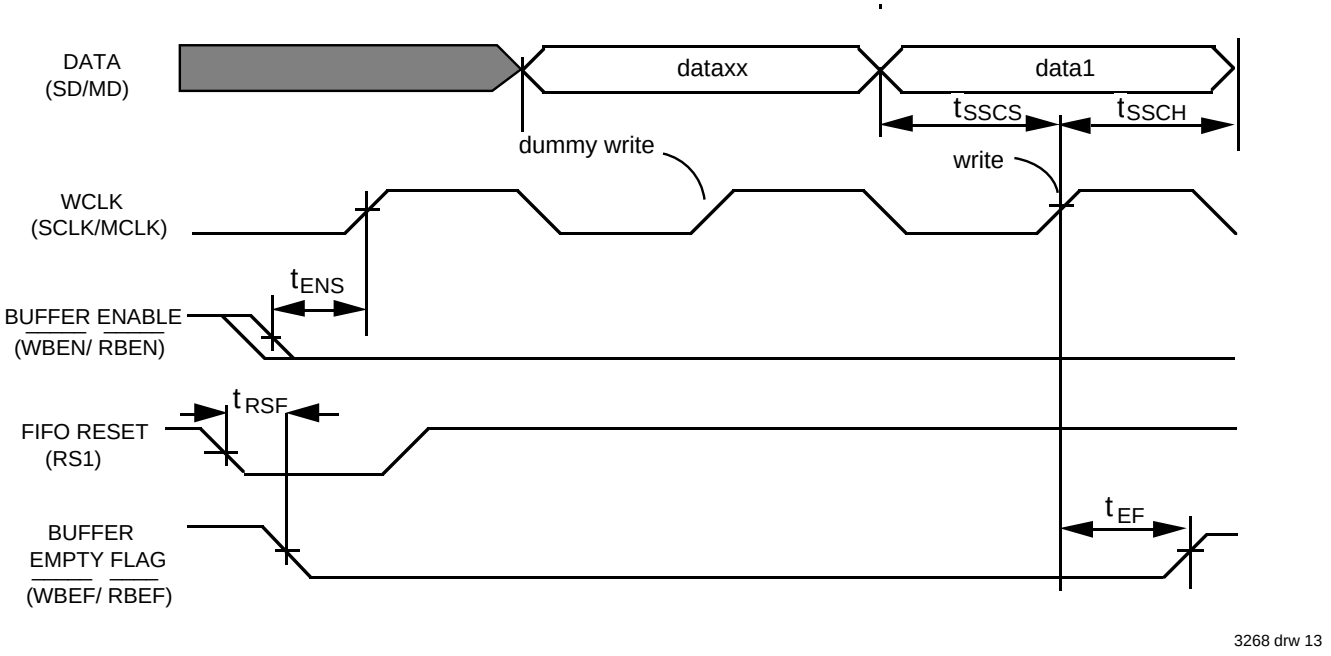


Figure 10. FIFO (WFIFO/RFIFO) Write Latency Timing

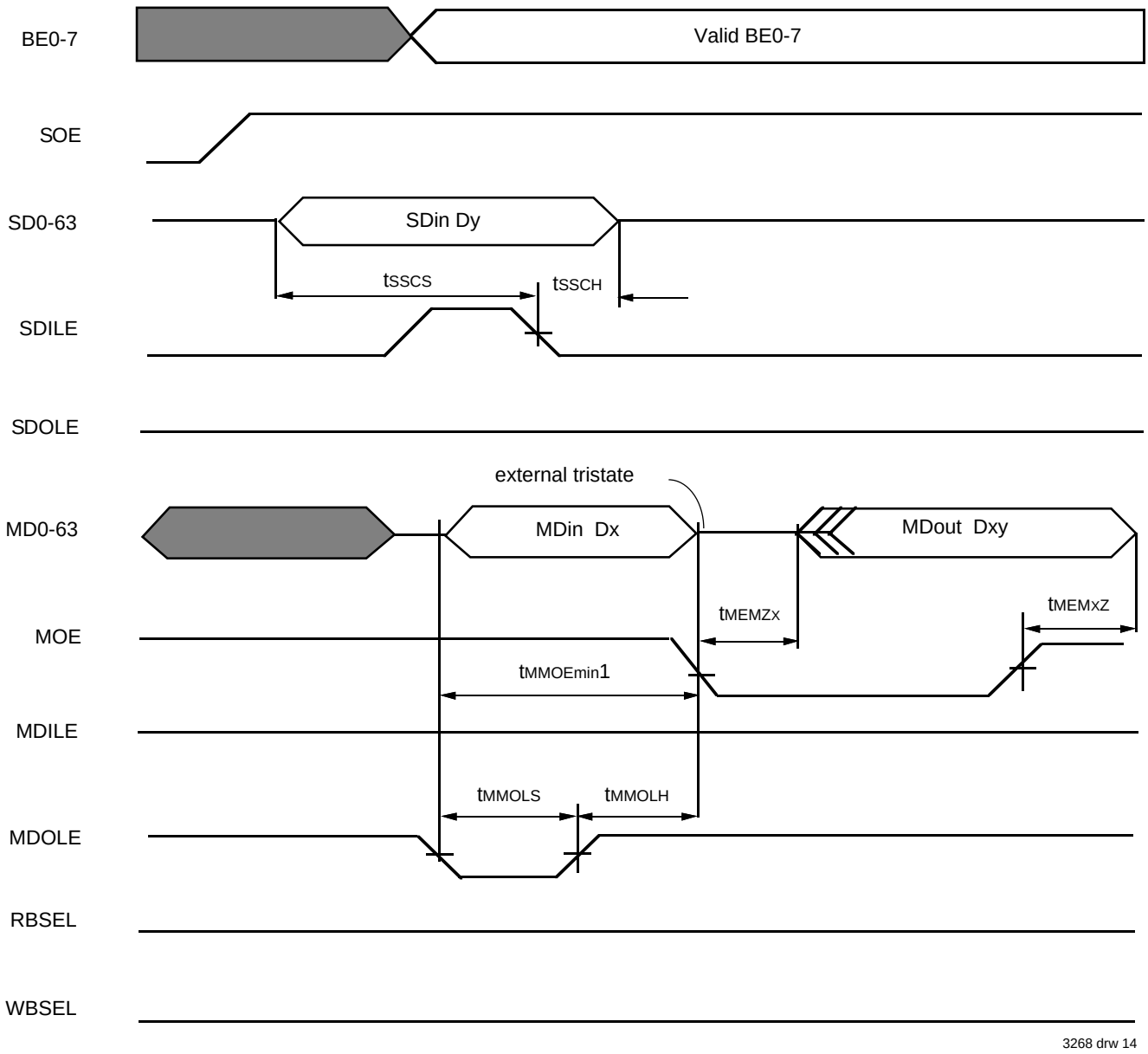


Figure 11. Partial Word Write/Byte Merge Timing

NOTE:
1. t_{MMOE} is not a propagation delay. For partial word write operations $t_{MMOE\ MIN} = t_{MDM}$.

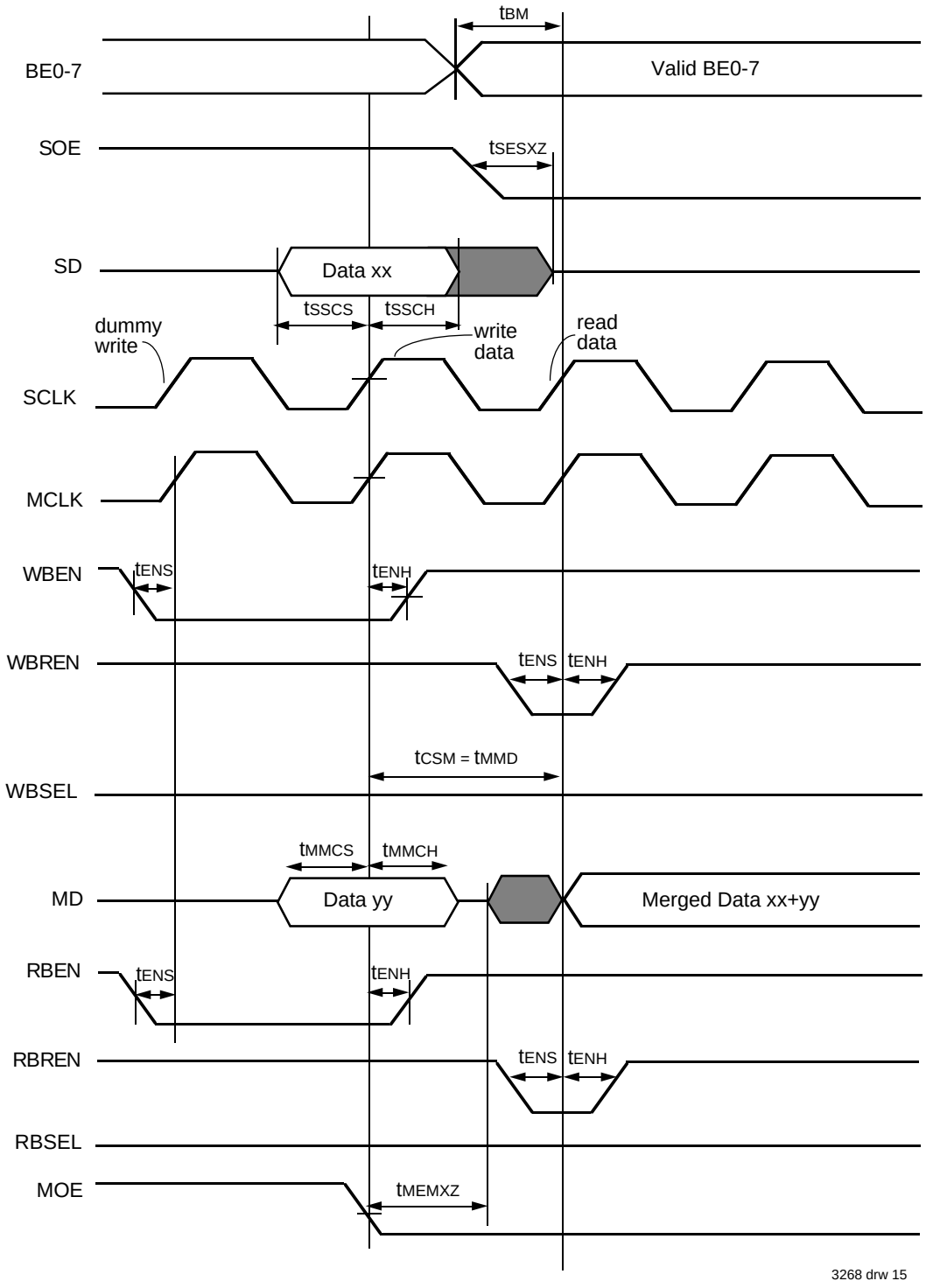


Figure 12. Partial Word Write/Byte Merge Timing using both RFIFO and WFIFO

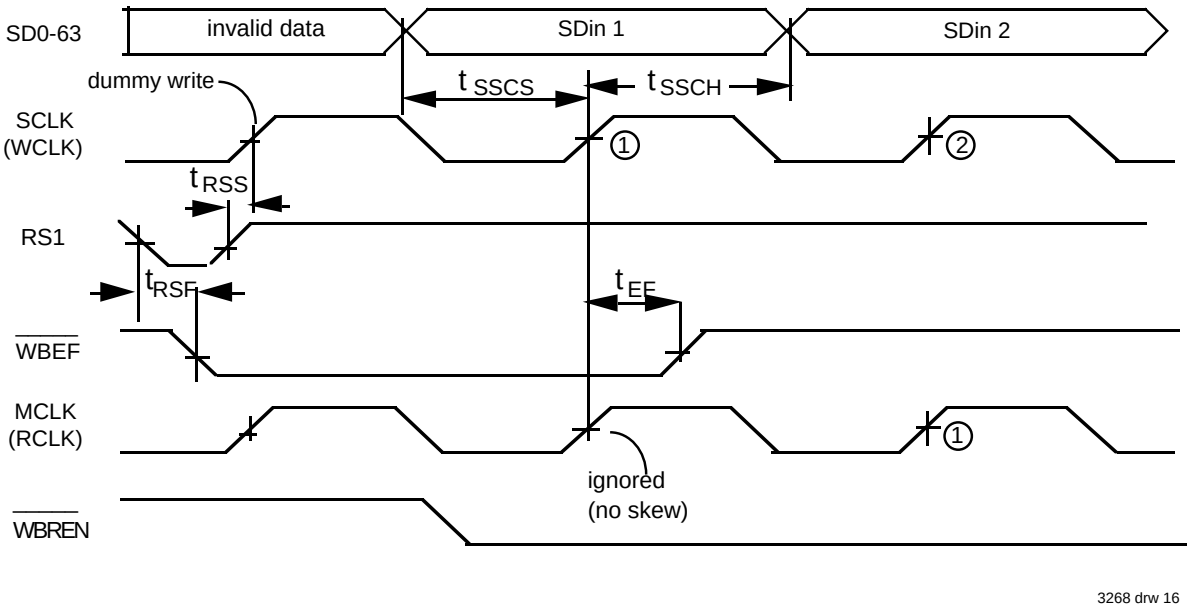


Figure 13. Write FIFO Write Timing with Clock Skew Violation

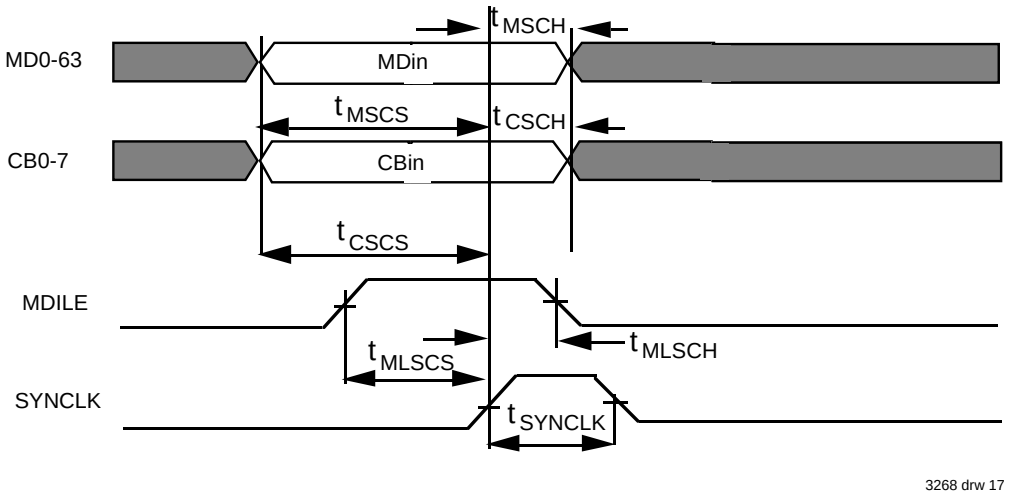
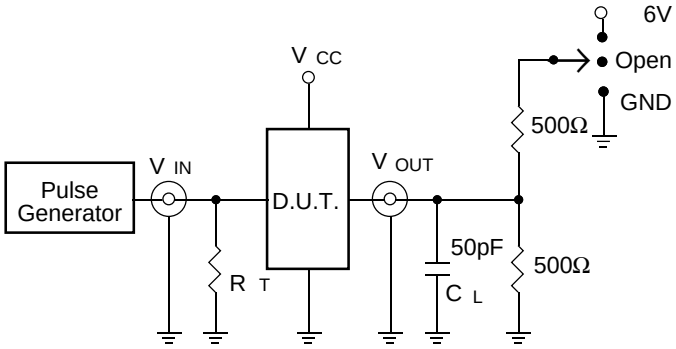


Figure 14. Diagnostic Timing

TEST CIRCUITS AND WAVEFORMS

TEST CIRCUITS FOR ALL OUTPUTS



3268 drw 18

SWITCH POSITION

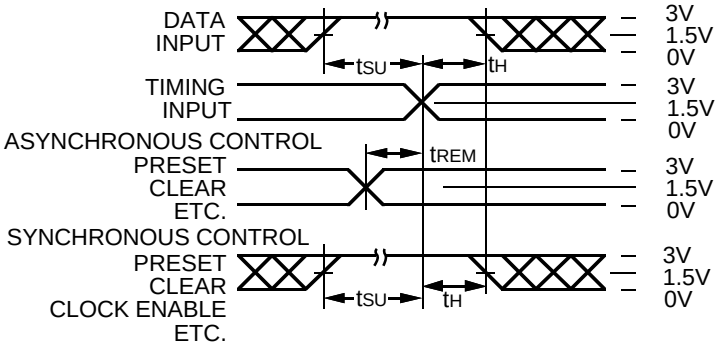
Test	Switch
Open Drain Disable Low Enable Low	6V
Disable High Enable High	GND
All Other tests	Open

2617 tbl 20

DEFINITIONS:

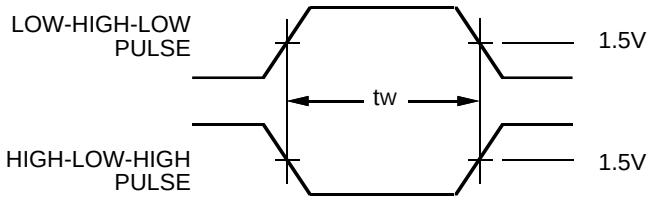
C_L = Load capacitance: includes jig and probe capacitance.
R_T = Termination resistance: should be equal to Z_{OUT} of the Pulse Generator.

SET-UP, HOLD AND RELEASE TIMES



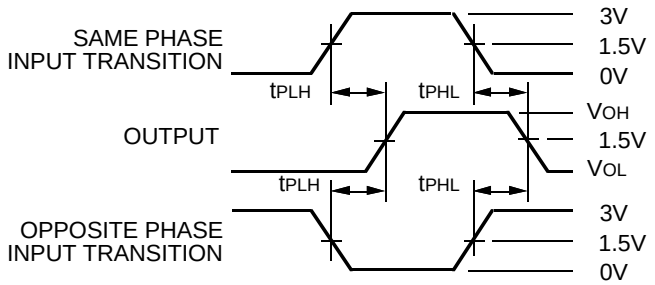
3268 drw 19

PULSE WIDTH



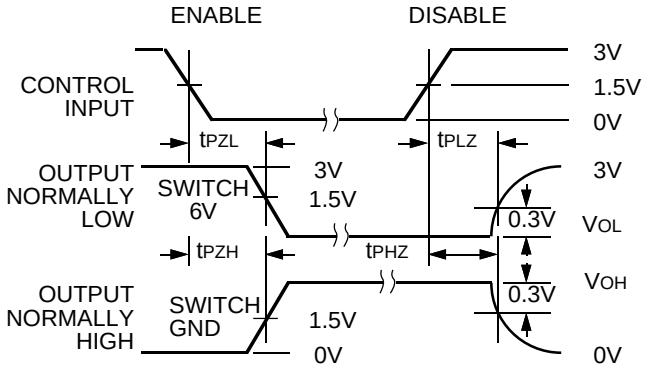
3268 drw 20

PROPAGATION DELAY



3268 drw 21

ENABLE AND DISABLE TIMES

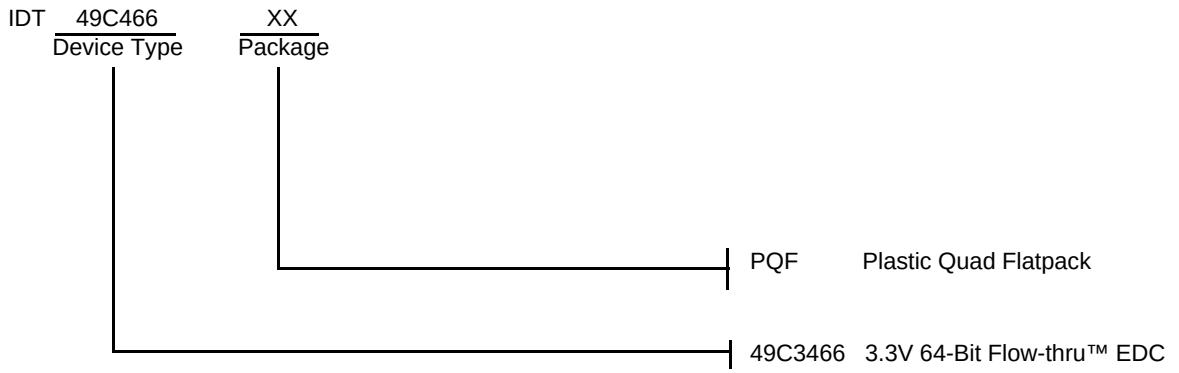


3268 drw 22

NOTES:

1. Diagram shown for input Control Enable-LOW and input Control Disable-HIGH.
2. Pulse Generator for All Pulses: Rate ≤ 1.0MHz; t_F ≤ 2.5ns; t_R ≤ 2.5ns.
3. If V_{CC} is below 3V, input voltage swings should be adjusted not to exceed V_{CC}.

ORDERING INFORMATION



3268 drw 23